## **EAST Search History**

Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L3	957	((trench recessg roove hole open\$3 mesa) near8 (polysilicon (poly near5 crystal\$3 near5 silicon)) near8 (polish\$3 CMP))	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:37
L4	471	3 and ((remov\$3 etch\$3) near5 (polysilicon (poly near5 crystal\$3 near5 silicon)) near8 (polish\$3 CMP))	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:38
L5	282	4 and temperature	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:03
L6	189	4 not 5	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:10
L8	565	((trench recessg roove hole open\$3 mesa) same (polysilicon (poly same crystal\$3 same silicon)) same (polish\$3 CMP))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/07/28 12:22
L9	488	8 and ((remov\$3 etch\$3) same (polysilicon (poly same crystal\$3 same silicon)) same (polish\$3 CMP))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/07/28 12:23
L10	4432583	(trench recessg groove hole open\$3 mesa)	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:37
L11	71317	10 and (polysilicon (poly near5 crystal\$3 near5 silicon))	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:38
L12	1899	11 and ((remov\$3 etch\$3) near5 (polysilicon (poly near5 crystal\$3 near5 silicon)) near8 (polish\$3 CMP))	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:39

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Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L3	957	((trench recessg roove hole open\$3 mesa) near8 (polysilicon (poly near5 crystal\$3 near5 silicon)) near8 (polish\$3 CMP))	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:22
L4	471	3 and ((remov\$3 etch\$3) near5 (polysilicon (poly near5 crystal\$3 near5 silicon)) near8 (polish\$3 CMP))	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:22
L5	282	4 and temperature	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:03
L6	189	4 not 5	US-PGPU B; USPAT; USOCR	OR	ON	2006/07/28 12:10
L8	565	((trench recessg roove hole open\$3 mesa) same (polysilicon (poly same crystal\$3 same silicon)) same (polish\$3 CMP))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/07/28 12:22
L9	488	8 and ((remov\$3 etch\$3) same (polysilicon (poly same crystal\$3 same silicon)) same (polish\$3 CMP))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/07/28 12:23